



New Product

Si4330DY
Vishay Siliconix

Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0165 at $V_{GS} = 10$ V	8.7
	0.022 at $V_{GS} = 4.5$ V	7.5

FEATURES

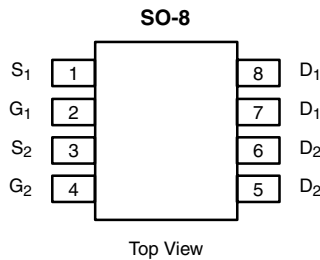
- TrenchFET® Power MOSFET
- 100 % R_G Tested



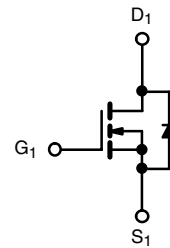
RoHS
COMPLIANT

APPLICATIONS

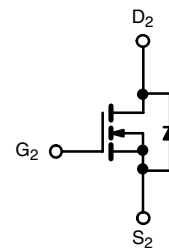
- Notebook
 - Load Switch
 - DC/DC Conversion
 - Auxiliary Voltage



Ordering Information: Si4330DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 sec	Steady State	Unit	
Drain-Source Voltage	V_{DS}	30		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	8.7	6.6	A
		$T_A = 70$ °C	7.0	5.3	
Pulsed Drain Current	I_{DM}	± 30		A	
Continuous Source Current (Diode Conduction) ^a	I_S	1.7	0.9		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	2.0	1.1	W
		$T_A = 70$ °C	1.3	0.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	45	62.5	°C/W
		Steady State	85	110	
Maximum Junction-to-Foot (Drain)	R_{thJF}	26	35		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.



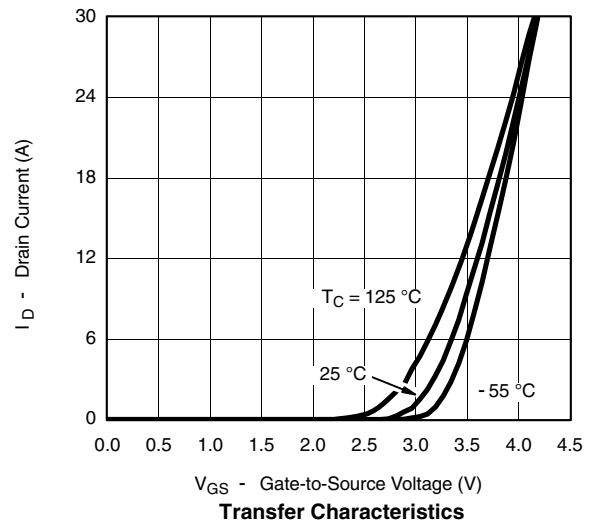
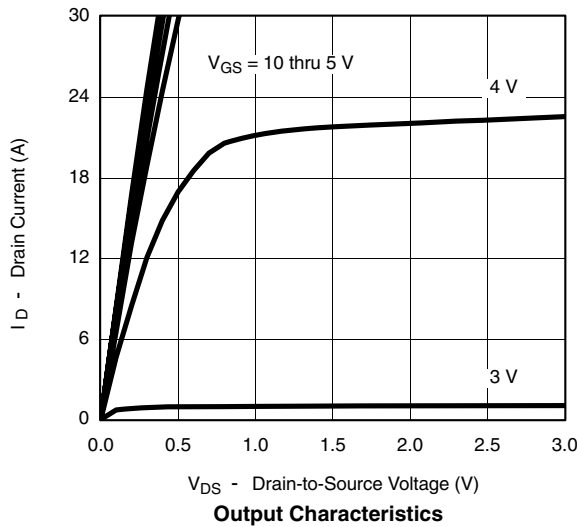
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8.7\text{ A}$		0.013	0.0165	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 7.5\text{ A}$		0.018	0.022	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 8.7\text{ A}$		28		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8.7\text{ A}$		13	20	nC
Gate-Source Charge	Q_{gs}		7.1			
Gate-Drain Charge	Q_{gd}		3.5			
Gate Resistance	R_g		0.5	1	1.7	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_G = 6\text{ }\Omega$		10	15	ns
Rise Time	t_r		10	15		
Turn-Off Delay Time	$t_{d(off)}$		40	60		
Fall Time	t_f		12	20		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		45	70	

Notes:

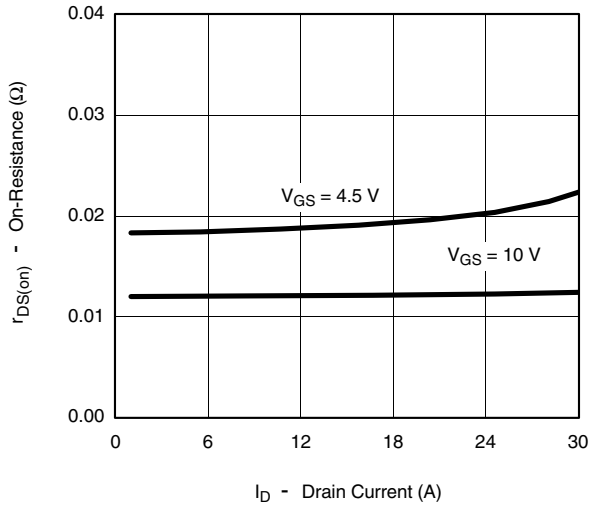
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

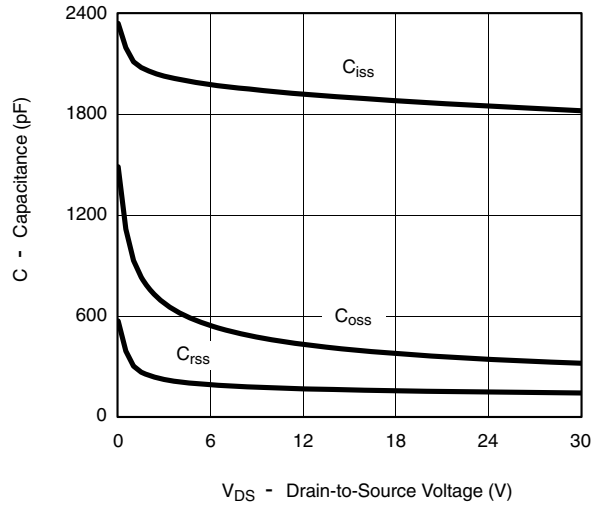
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



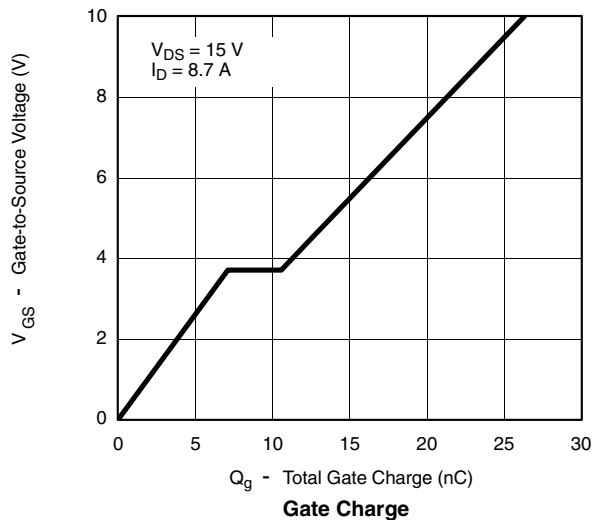
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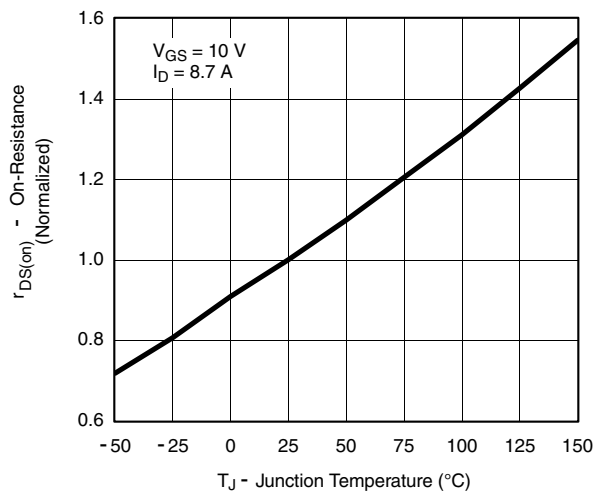
On-Resistance vs. Drain Current



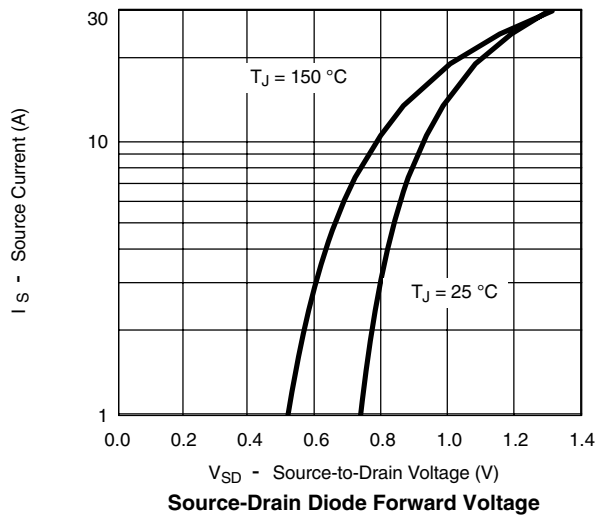
Capacitance



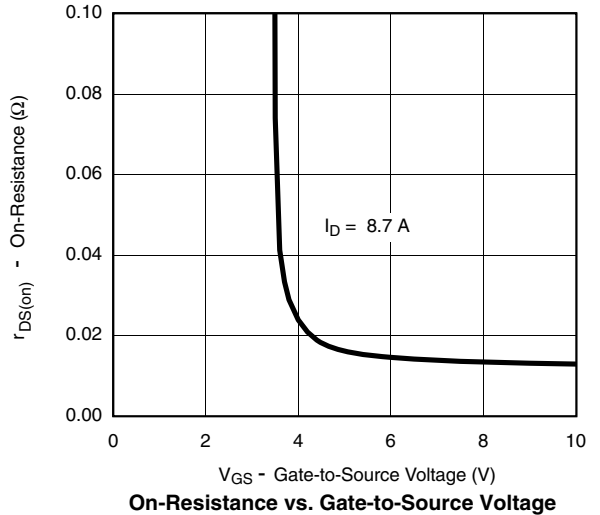
Gate Charge



On-Resistance vs. Junction Temperature

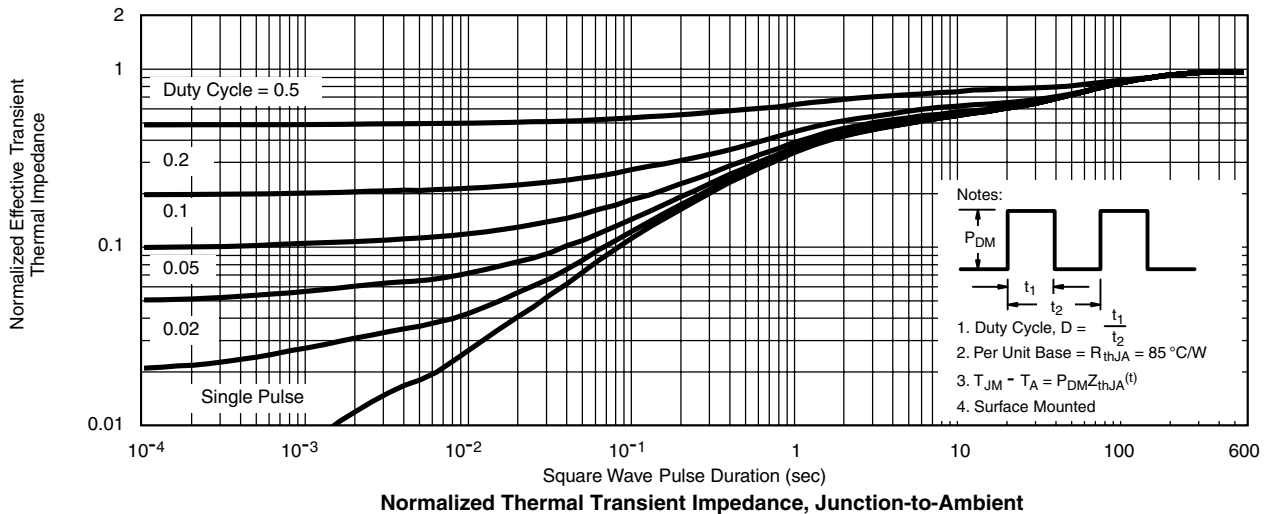
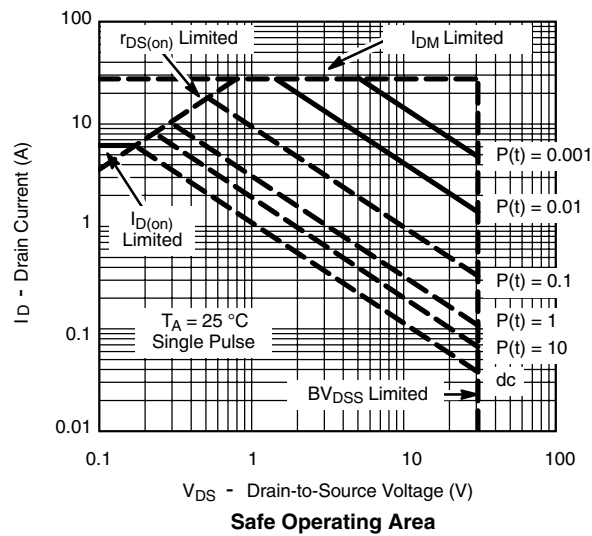
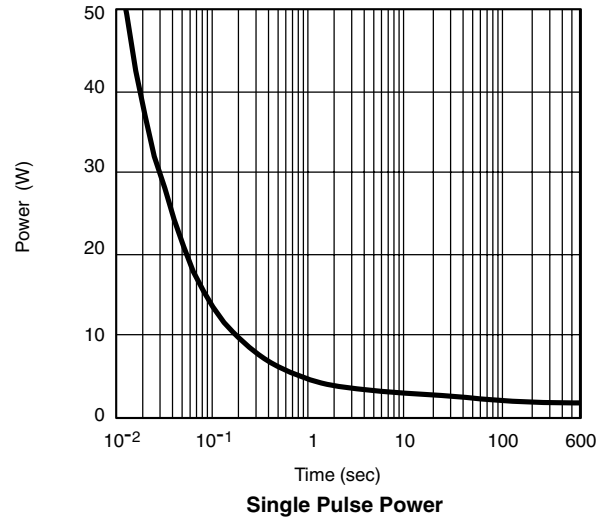
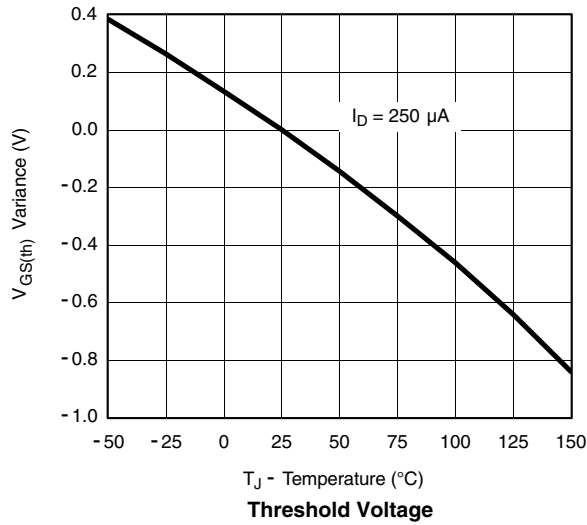


Source-Drain Diode Forward Voltage



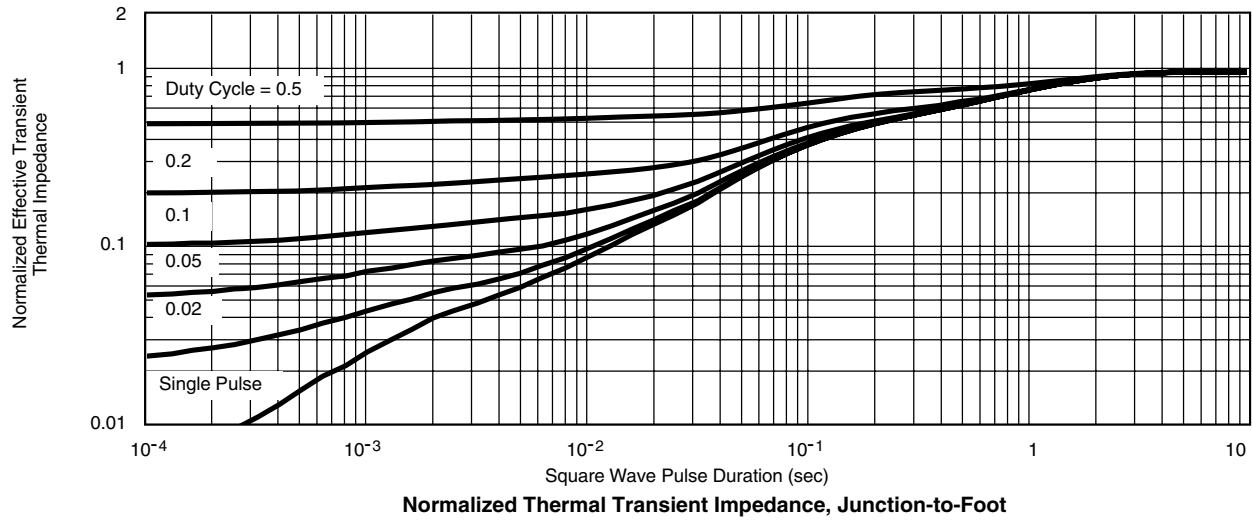
On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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